

Switchmode Dual Ultrafast Power Rectifiers

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage , High Current Capability
 * High-Switching Speed 50 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory

MAXIMUM RATINGS

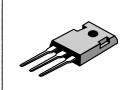
Characteristic	Symbol	U60D				Unit
		05	10	15	20	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	150	200	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	105	140	V
Average Rectifier Forward Current Per Leg T _c =125°C Per Total Device	I _{F(AV)}		_	30 60		A
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz, T _c =125°C)	I _{FM}		6	60		Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	 FSM		50	00		А
Operating and Storage Junction Temperature Range	T _j , T _{stg}		- 65 tc	+ 150		°C

ELECTRICAL CHARACTERISTICS

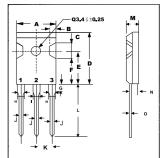
Characteristic	Symbol	U60D				Unit
		05	10	15	20	
Maximum Instantaneous Forward Voltage $(I_F=30 \text{ Amp}, T_C=25 ^{\circ}\text{C})$ $(I_F=30 \text{ Amp}, T_C=100 ^{\circ}\text{C})$	V _F			00 85		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _c = 25 °C) (Rated DC Voltage, T _c = 125 °C)	I _R		-	5 .5		uA mA
Reverse Recovery Time (I _F = 0.5 A, I _R =1.0 , I _{rr} =0.25 A)	T _{rr}		Ę	50		ns
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P		62	20		pF

ULTRA FAST RECTIFIERS

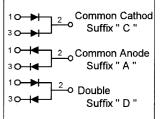
60 AMPERES 50 -- 200 VOLTS



TO-247 (3P)



DIM	MILLMETERS		
Dilvi	MIN	MAX	
Α		16.2	
В	1.7	2.7	
С	5.0	6.0	
D		23.0	
Ε	14.8	15.2	
F	11.7	12.7	
G		4.5	
Н		2.5	
- 1		3.5	
J	1.1	1.4	
K	5.25	5.65	
L	19		
M	4.7	5.3	
N	2.8	3.2	
0	0.45	0.85	



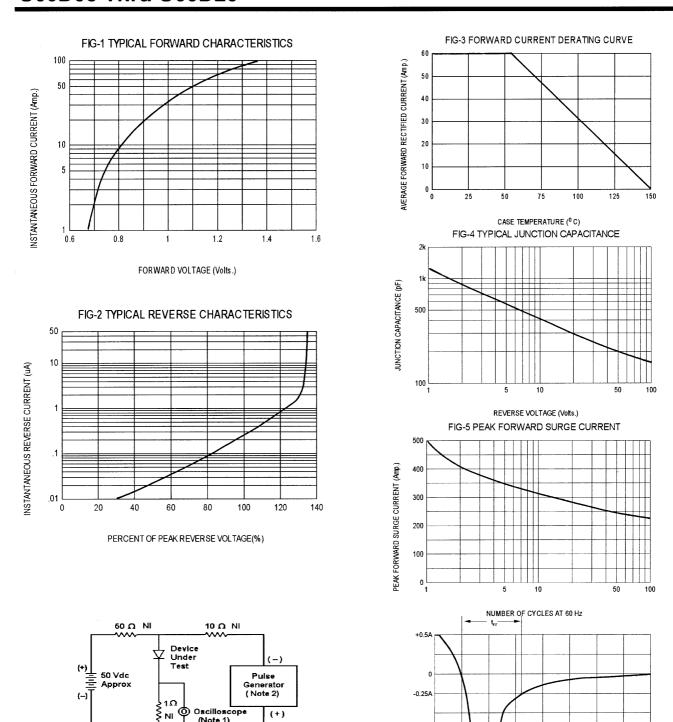


Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram

-1.0A

Set time base for 20 ns/div

Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50 Ω



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